

December 9, 2003

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

**Continuation Application of**  
Serial No.: 10/002,031 11/30/01

YEE-CHIA YEO, CHUN CHIEH LIN, FU-LIANG YANG,  
CHEN MING HU

COMPLEMENTARY METAL OXIDE SEMICONDUCTOR  
TRANSISTOR TECHNOLOGY USING SELECTIVE  
EPITAXY OF A STRAINED SILICON GERMANIUM  
LAYER

**PRELIMINARY AMENDMENT**

Dear Sir:

This is a preliminary amendment for the above referenced Continuation Application.

Please amend the above identified application for patent as follows:

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on December 9, 2003.

Stephen B. Ackerman, Reg. No. 37,761

Signature/Date



12/9/03

October 24, 2003

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Fr: Stephen B. Ackerman, Reg. No. 37,761  
28 Davis Ave.  
Poughkeepsie, N.Y. 12603

**CONTINUATION OF:**

Subject: Serial No. 10/002,031

File Date: 11/30/01

Inventor: Y. C. Yeo et al

Examiner: C.W. Lattin

Art Unit: 2812

Title: "COMPLEMENTARY METAL OXIDE SEMICONDUCTOR TRANSISTOR  
TECHNOLOGY USING SELECTIVE EPITAXY OF A STRAINED SILICON  
GERMANIUM LAYER"

**PRELIMINARY AMENDMENT**

Dear Sir;

Please enter the attached preliminary amendment, for the above-intended application for patent.

The commissioner is hereby authorized to charge payment of any additional fees involved with added Claims and the like to Deposit Account No. 19-0033

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on Dec. 9, 2003.

Stephen B. Ackerman, Reg. No. 37,761

Signature 

Date 12/19/03